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FAIRCHILD SEMICONDUCTOR®

July 2010

FDN8601

N-Channel PowerTrench® MOSFET

100 V, 2.7 A, 109 mΩ

Features

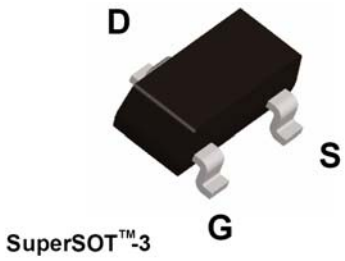
- Max $r_{DS(on)}$ = 109 mΩ at V_{GS} = 10 V, I_D = 1.5 A
- Max $r_{DS(on)}$ = 175 mΩ at V_{GS} = 6 V, I_D = 1.2 A
- High performance trench technology for extremely low $r_{DS(on)}$
- High power and current handling capability in a widely used surface mount package
- Fast switching speed
- 100% UIL tested
- RoHS Compliant

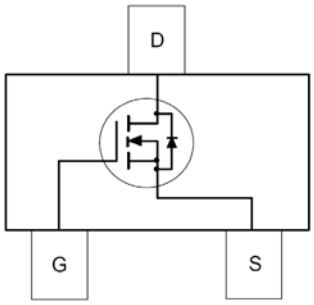
General Description

This N-Channel MOSFET is produced using Fairchild Semiconductor's advanced Power Trench® process that has been optimized for $r_{DS(on)}$, switching performance and ruggedness.

Applications

- Primary DC-DC Switch
- Load Switch





MOSFET Maximum Ratings T_A = 25 °C unless otherwise noted

Symbol	Parameter		Ratings	Units
V_{DS}	Drain to Source Voltage		100	V
V_{GS}	Gate to Source Voltage		±20	V
I_D	-Continuous	(Note 1a)	2.7	A
	-Pulsed		12	
E_{AS}	Single Pulse Avalanche Energy	(Note 3)	13	mJ
P_D	Power Dissipation	(Note 1a)	1.5	W
	Power Dissipation	(Note 1b)	0.6	
T_J, T_{STG}	Operating and Storage Junction Temperature Range		-55 to +150	°C

Thermal Characteristics

$R_{\theta JC}$	Thermal Resistance, Junction to Case	(Note 1)	75	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	(Note 1a)	80	

Package Marking and Ordering Information

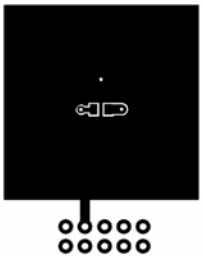
Device Marking	Device	Package	Reel Size	Tape Width	Quantity
8601	FDN8601	SSOT-3	7 ”	8 mm	3000 units

Electrical Characteristics T_J = 25 °C unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
Off Characteristics						
BV_{DSS}	Drain to Source Breakdown Voltage	I_D = 250 μA, V_{GS} = 0 V	100			V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	I_D = 250 μA, referenced to 25 °C		68		mV/°C
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS} = 80 V, V_{GS} = 0 V			1	μA
I_{GSS}	Gate to Source Leakage Current	V_{GS} = ±20 V, V_{DS} = 0 V			±100	nA
On Characteristics (Note 2)						
$V_{GS(th)}$	Gate to Source Threshold Voltage	V_{GS} = V_{DS}, I_D = 250 μA	2.0	3.0	4.0	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate to Source Threshold Voltage Temperature Coefficient	I_D = 250 μA, referenced to 25 °C		-8		mV/°C
$r_{DS(on)}$	Static Drain to Source On Resistance	V_{GS} = 10 V, I_D = 1.5 A		85.4	109	mΩ
		V_{GS} = 6 V, I_D = 1.2 A		117	175	
		V_{GS} = 10 V, I_D = 1.5 A, T_J = 125 °C		143	183	
g_{FS}	Forward Transconductance	V_{DS} = 10 V, I_D = 1.5 A		8		S
Dynamic Characteristics						
C_{iss}	Input Capacitance	V_{DS} = 50 V, V_{GS} = 0 V, f = 1 MHz		156	210	pF
C_{oss}	Output Capacitance			47	65	pF
C_{rss}	Reverse Transfer Capacitance			2.7	5	pF
R_g	Gate Resistance			1.0		Ω
Switching Characteristics						
$t_{d(on)}$	Turn-On Delay Time	V_{DD} = 50 V, I_D = 1.5 A, V_{GS} = 10 V, R_{GEN} = 6 Ω		4.3	10	ns
t_r	Rise Time			1.3	10	ns
$t_{d(off)}$	Turn-Off Delay Time			7.8	16	ns
t_f	Fall Time			3.4	10	ns
Q_g	Total Gate Charge	V_{GS} = 0 V to 10 V; V_{DD} = 50 V, I_D = 1.5 A		3	5	nC
Q_g	Total Gate Charge	V_{GS} = 0 V to 5 V; V_{DD} = 50 V, I_D = 1.5 A		1.8	3	nC
Q_{gs}	Gate to Source Gate Charge	V_{DD} = 50 V, I_D = 1.5 A		0.9		nC
Q_{gd}	Gate to Drain “Miller” Charge	V_{DD} = 50 V, I_D = 1.5 A		0.8		nC
Drain-Source Diode Characteristics						
V_{SD}	Source to Drain Diode Forward Voltage	V_{GS} = 0 V, I_S = 1.5 A (Note 2)		0.81	1.3	V
t_{rr}	Reverse Recovery Time	I_F = 1.5 A, di/dt = 100 A/μs		29	46	ns
Q_{rr}	Reverse Recovery Charge			15	27	nC

Notes:

1. $R_{\theta JA}$ is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. $R_{\theta JC}$ is guaranteed by design while $R_{\theta CA}$ is determined by the user's board design.



a) 80 °C/W when mounted on a 1 in^2 pad of 2 oz copper

b) 180 °C/W when mounted on a minimum pad.

2. Pulse Test: Pulse Width < 300 μs, Duty cycle < 2.0%.

3. Starting T_J = 25 °C; N-ch: L = 3 mH, I_{AS} = 3 A, V_{DD} = 100 V, V_{GS} = 10 V.

Typical Characteristics T_J = 25 °C unless otherwise noted

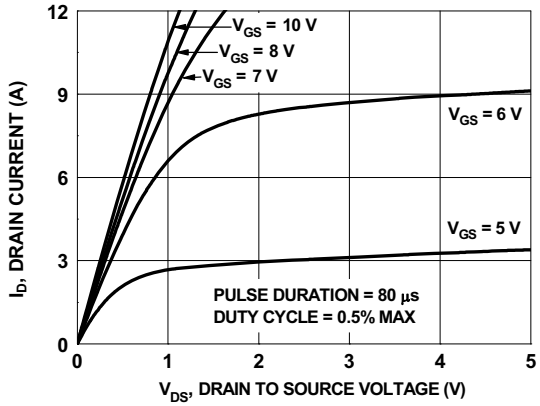


Figure 1. On-Region Characteristics

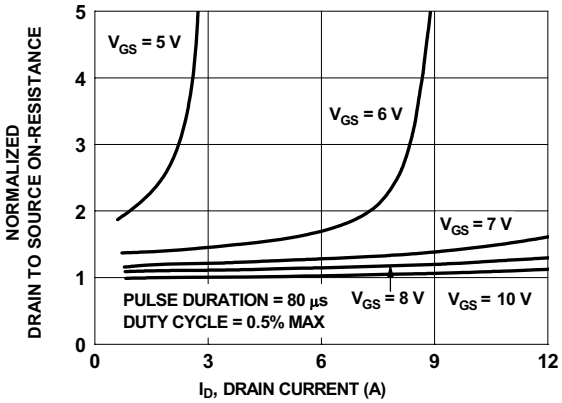


Figure 2. Normalized On-Resistance vs Drain Current and Gate Voltage

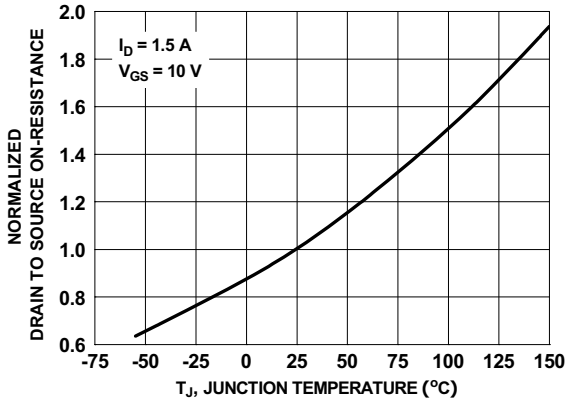


Figure 3. Normalized On-Resistance vs Junction Temperature

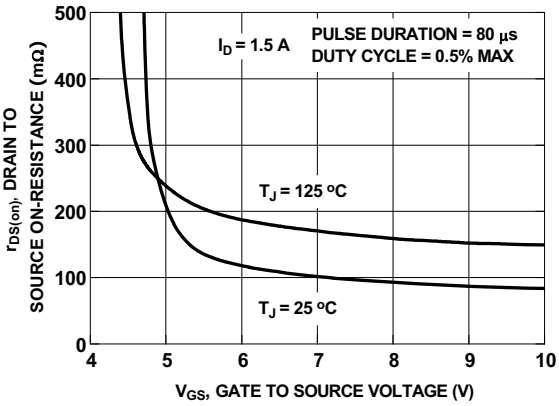


Figure 4. On-Resistance vs Gate to Source Voltage

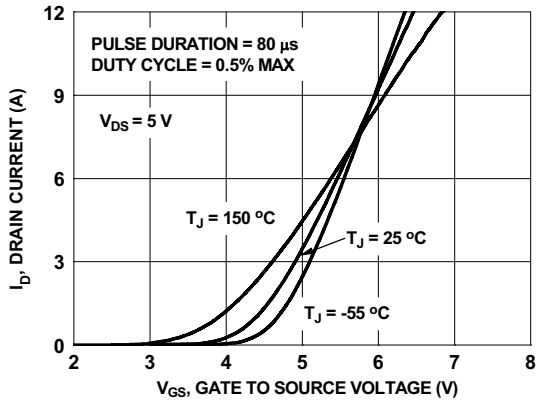


Figure 5. Transfer Characteristics

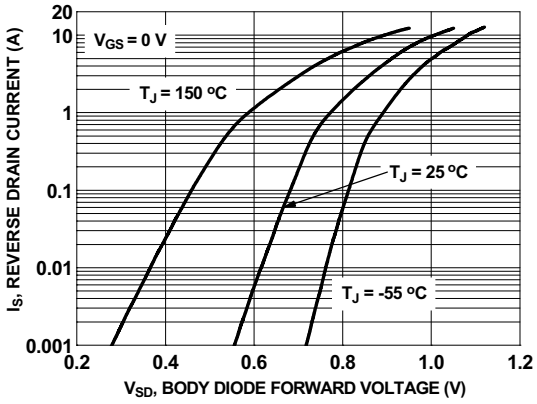


Figure 6. Source to Drain Diode Forward Voltage vs Source Current

Typical Characteristics T_J = 25 °C unless otherwise noted

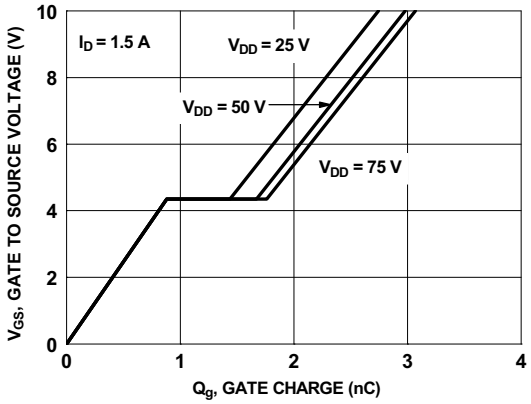


Figure 7. Gate Charge Characteristics

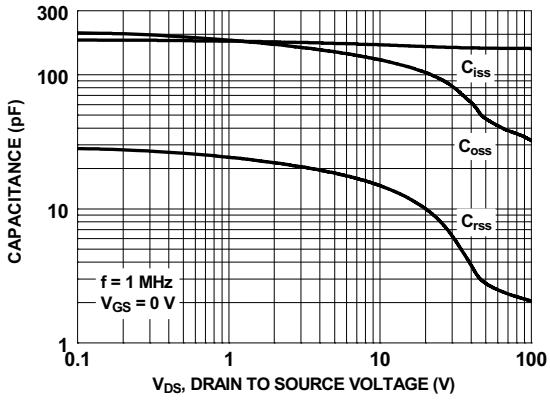


Figure 8. Capacitance vs Drain to Source Voltage

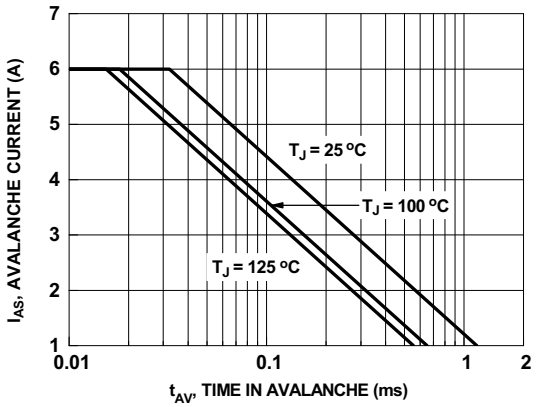


Figure 9. Unclamped Inductive Switching Capability

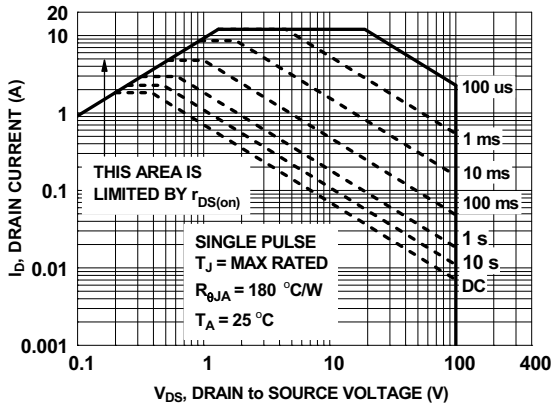


Figure 10. Forward Bias Safe Operating Area

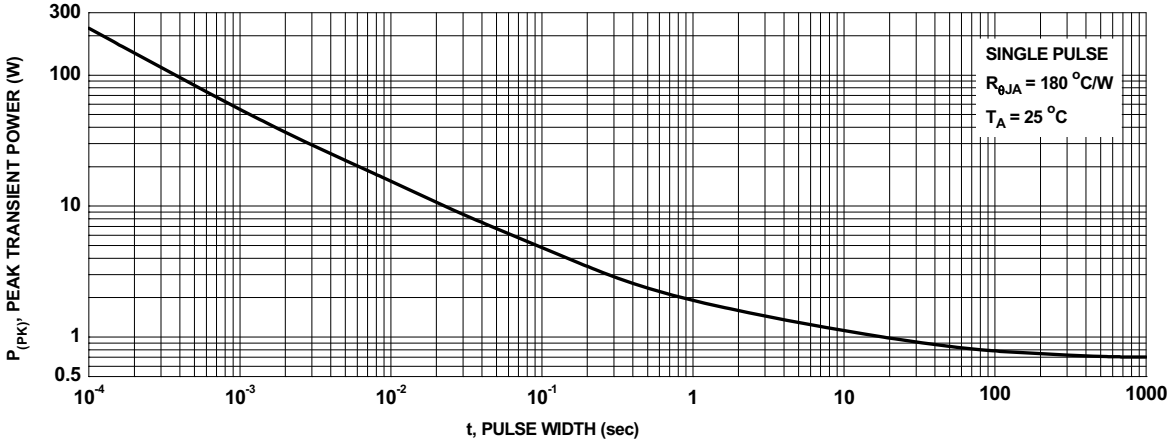


Figure 11. Single Pulse Maximum Power Dissipation

Typical Characteristics T_J = 25 °C unless otherwise noted

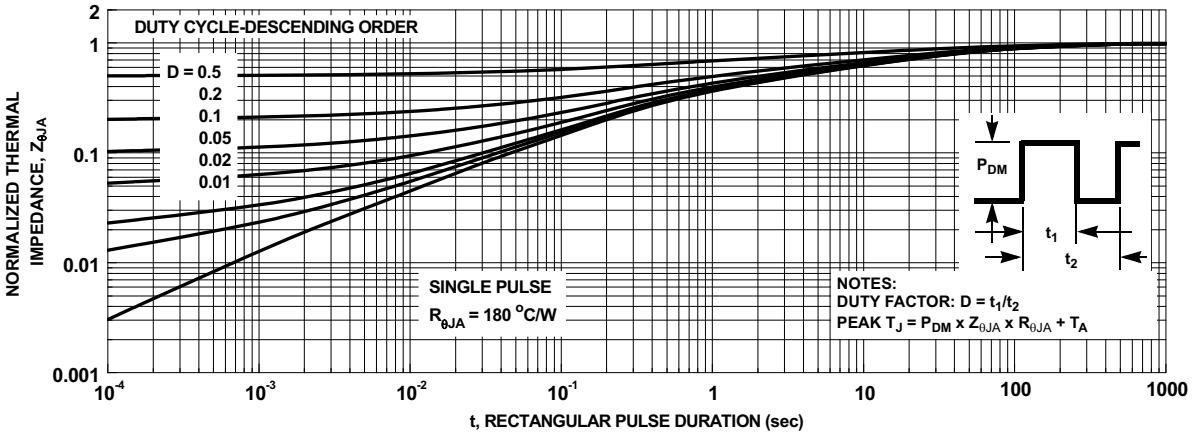


Figure 12. Junction-to-Ambient Transient Thermal Response Curve

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Obsolete	Not In Production	Datasheet contains specifications on a product that is discontinued by Fairchild Semiconductor. The datasheet is for reference information only.

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